



Rev. 1.1

UTRON

UT62L12816(I)

128K X 16 BIT LOW POWER CMOS SRAM

REVISION HISTORY

REVISION	DESCRIPTION	DATE
Preliminary Rev. 0.5	Original.	Mar, 2001
Preliminary Rev. 0.6	1. The symbols CE# and OE# and WE# are revised as $\overline{CE}$ and $\overline{OE}$ and $\overline{WE}$. 2. Separate Industrial and Consumer SPEC. 3. Add access time 55ns range.	Jun 21,2001
Preliminary Rev. 0.7	1. Revised Vcc range : a、 55ns (max.) for Vcc=2.7V~3.6V b、 70/100ns (max.) for Vcc=2.5V~3.6V 2. Revised block diagram 3. Revised DC ELECTRICAL CHARACTERISTICS : c、 Revised standby current $I_{SB1}=20/3\mu A(\text{max.})$ for $T_A=0^{\circ}\text{C}\sim 50^{\circ}\text{C}$ $I_{SB2}=80/10\mu A(\text{max.})$ for $T_A=-40^{\circ}\text{C}\sim 85^{\circ}\text{C}$ d、 Revised Icc=35/30/25mA(max.) 4. Revised AC ELECTRICAL CHARACTERISTICS : e、 Revised symbol name t_{HZB} as t_{BHZ} f、 Revised symbol name t_{LZB} as t_{BLZ} g、 Revised symbol name t_{PWB} as t_{BW} 5. Revised waveforms 6. Revised $I_{DR}=50/5\mu A(\text{max.})$	Nov 6, 2001
Rev. 1.0	1. Revised DC ELECTRICAL CHARACTERISTICS : a、 Revised V_{IH} as 2.2V 2. Revised AC ELECTRICAL CHARACTERISTICS : b、 Revised t_{BLZ} as 10ns (min.) 3. Revised 48-pin TFBGA package outline dimension : c、 Rev. 0.7 : ball diameter=0.3mm d、 Rev. 1.0 : ball diameter=0.35mm	Apr 23,2002
Rev. 1.1	Add order information for lead free product	May 09,2003



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FEATURES

- Fast access time :
 - 55ns (max.) for $V_{CC}=2.7V\sim 3.6V$
 - 70/100ns (max.) for $V_{CC}=2.5V\sim 3.6V$
- CMOS low power operating
 - Operating current : 35/30/25mA (I_{CC} max.)
 - Standby current :
 - 20uA(max.) L-version, $0^{\circ}C \leq T_A \leq 50^{\circ}C$
 - 3uA(max.) LL-version, $0^{\circ}C \leq T_A \leq 50^{\circ}C$
- Single 2.5V~3.6V power supply
- Operating temperature:
 - Industrial : $-40^{\circ}C \sim 85^{\circ}C$
- All TTL compatible inputs and outputs
- Fully static operation
- Three state outputs
- Data retention voltage : 1.5V (min.)
- Data byte control : $\overline{LB}$ (I/O1~I/O8)
 $\overline{UB}$ (I/O9~I/O16)
- Package : 44-pin 400mil TSOP-II
 48-pin 6mm × 8mm TFBGA

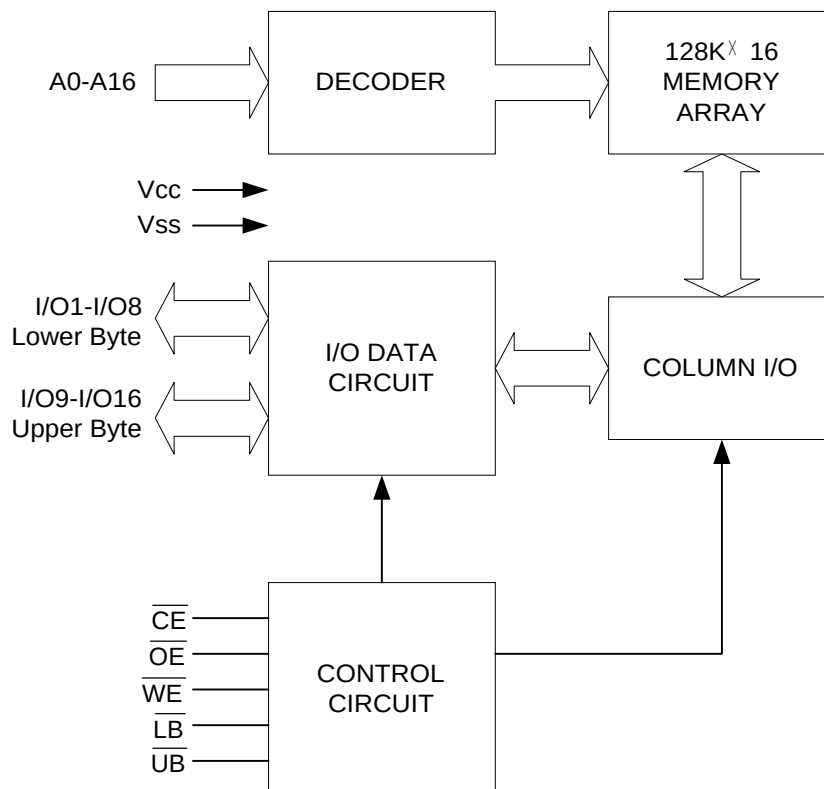
GENERAL DESCRIPTION

The UT62L12816(I) is a 2,097,152-bit low power CMOS static random access memory organized as 131,072 words by 16 bits.

The UT62L12816(I) operates from a wide range of 2.5V~ 3.6V supply voltage and all inputs and outputs are fully TTL compatible.

The UT62L12816(I) is designed for low power system applications.

FUNCTIONAL BLOCK DIAGRAM



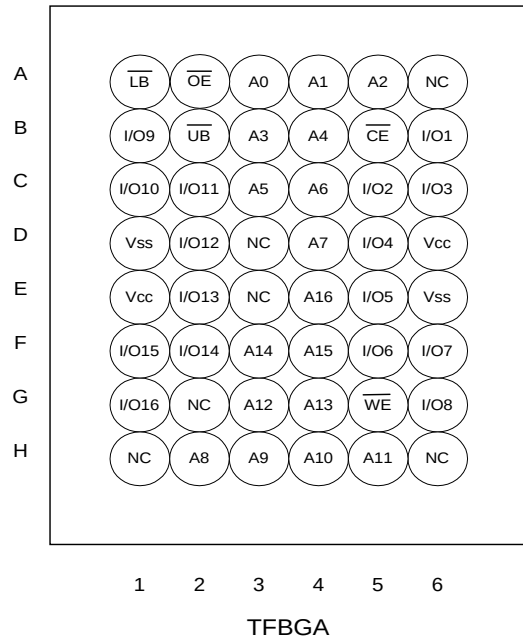
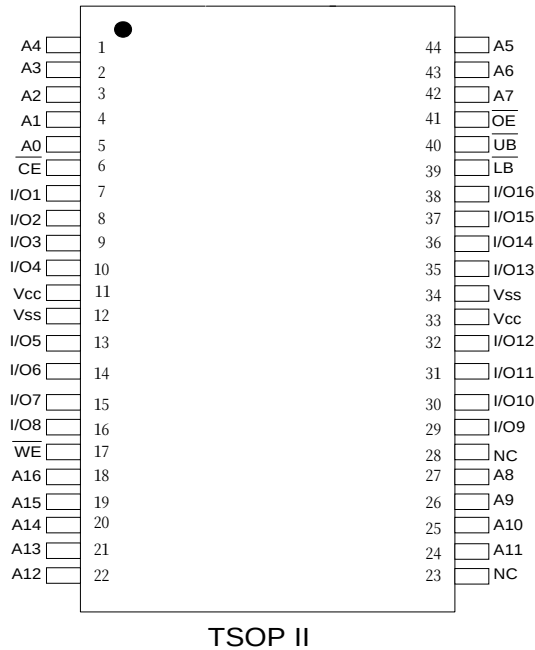


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PIN CONFIGURATION



PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0 - A16	Address Inputs
I/O1 - I/O16	Data Inputs/Outputs
$\overline{CE}$	Chip Enable Input
$\overline{WE}$	Write Enable Input
$\overline{OE}$	Output Enable Input
$\overline{LB}$	Lower Byte Control
$\overline{UB}$	Upper Byte Control
V_{CC}	Power Supply
V_{SS}	Ground
NC	No Connection

TRUTH TABLE

MODE	$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	$\overline{LB}$	$\overline{UB}$	I/O OPERATION		SUPPLY CURRENT
						I/O1-I/O8	I/O9-I/O16	
Standby	H	X	X	X	X	High - Z	High - Z	I_{SB}, I_{SB1}, I_{SB2}
	X	X	X	H	H	High - Z	High - Z	
Output Disable	L	H	H	L	X	High - Z	High - Z	I_{CC}, I_{CC1}, I_{CC2}
	L	H	H	X	L	High - Z	High - Z	
Read	L	L	H	L	H	D_{OUT}	High - Z	I_{CC}, I_{CC1}, I_{CC2}
	L	L	H	H	L	High - Z	D_{OUT}	
	L	L	H	L	L	D_{OUT}	D_{OUT}	
Write	L	X	L	L	H	D_{IN}	High - Z	I_{CC}, I_{CC1}, I_{CC2}
	L	X	L	H	L	High - Z	D_{IN}	
	L	X	L	L	L	D_{IN}	D_{IN}	

Note: H = VIH, L = VIL, X = Don't care.



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ABSOLUTE MAXIMUM RATINGS*

PARAMETER	SYMBOL	RATING	UNIT
Terminal Voltage with Respect to V_{SS}	V_{TERM}	-0.3 to $V_{CC}+0.3V$	V
Operating Temperature	T_A	-40 to 85	°C
Storage Temperature	T_{STG}	-65 to 150	°C
Power Dissipation	P_D	1	W
DC Output Current	I_{OUT}	50	mA
Soldering Temperature (under 10 secs)	T_{solder}	260	°C

*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.

DC ELECTRICAL CHARACTERISTICS ($V_{CC} = 2.5V \sim 3.6V$, $T_A = -40^\circ C$ to $85^\circ C$)

PARAMETER	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Power Voltage	Vcc		55	2.7V	3.0V	3.6V	V
			70/100	2.5V	-	3.6V	V
Input High Voltage	V _{IH} ^{*1}			2.2	-	V _{CC} +0.3	V
Input Low Voltage	V _{IL} ^{*2}			-0.3	-	0.6	V
Input Leakage Current	I _{LI}	V _{SS} ≤V _{IN} ≤V _{CC}		- 1	-	1	μA
Output Leakage Current	I _{LO}	V _{SS} ≤V _{I/O} ≤V _{CC} ; Output Disable		- 1	-	1	μA
Output High Voltage	V _{OH}	I _{OH} = -1mA , (I _{OH} = -0.5mA when Vcc<2.7V)		2.2	-	-	V
Output Low Voltage	V _{OL}	I _{OL} = 2.1mA		-	-	0.4	V
Operating Power Supply Current	I _{CC}	Cycle time=min, 100%duty I/O=0mA, $\overline{CE}$ =V _{IL}	55	-	20	35	mA
			70	-	18	30	mA
			100	-	15	25	mA
Average Operation Current	I _{CC1}	100%duty, I _{I/O} =0mA $\overline{CE} \leq 0.2V$, other pins at 0.2V or Vcc-0.2V	TCycle=1μs	-	4	5	mA
	I _{CC2}		TCycle=500ns	-	8	10	mA
Standby Current (TTL)	I _{SB}	$\overline{CE}$ =V _{IH} , other pins =V _{IL} or V _{IH}		-	0.3	0.5	mA
Standby Current (CMOS)	I _{SB1}	$\overline{CE}$ =V _{CC} -0.2V, T _A = 0°C to 50°C other pins at 0.2V or Vcc-0.2V	-L	-	-	20	μA
			-LL	-	-	3	μA
	I _{SB2}	$\overline{CE}$ =V _{CC} -0.2V, T _A = -40°C to 85°C other pins at 0.2V or Vcc-0.2V	-L	-	-	80	μA
			-LL	-	-	10	μA

Notes:

1. Overshoot : $V_{CC}+3.0v$ for pulse width less than 10ns.
2. Undershoot : $V_{SS}-3.0v$ for pulse width less than 10ns.
3. Overshoot and Undershoot are sampled, not 100% tested.



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CAPACITANCE ($T_A=25^{\circ}\text{C}$, $f=1.0\text{MHz}$)

PARAMETER	SYMBOL	MIN.	MAX	UNIT
Input Capacitance	C_{IN}	-	6	pF
Input/Output Capacitance	$C_{I/O}$	-	8	pF

Note : These parameters are guaranteed by device characterization, but not production tested.

AC TEST CONDITIONS

Input Pulse Levels	0V to 3.0V
Input Rise and Fall Times	5ns
Input and Output Timing Reference Levels	1.5V
Output Load	$C_L = 30\text{pF}$, $I_{OH}/I_{OL} = -1\text{mA}/2.1\text{mA}$

AC ELECTRICAL CHARACTERISTICS ($T_A = -40^{\circ}\text{C}$ to 85°C)

(1) READ CYCLE

PARAMETER	SYMBOL	UT62L12816(I)-55 $V_{CC} = 2.7\text{V} \sim 3.6\text{V}$		UT62L12816(I)-70 $V_{CC} = 2.5\text{V} \sim 3.6\text{V}$		UT62L12816(I)-100 $V_{CC} = 2.5\text{V} \sim 3.6\text{V}$		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Read Cycle Time	t_{RC}	55	-	70	-	100	-	ns
Address Access Time	t_{AA}	-	55	-	70	-	100	ns
Chip Enable Access Time	t_{ACE}	-	55	-	70	-	100	ns
Output Enable Access Time	t_{OE}	-	30	-	35	-	50	ns
Chip Enable to Output in Low Z	t_{CLZ}^*	10	-	10	-	10	-	ns
Output Enable to Output in Low Z	t_{OLZ}^*	5	-	5	-	5	-	ns
Chip Disable to Output in High Z	t_{CHZ}^*	-	20	-	25	-	30	ns
Output Disable to Output in High Z	t_{OHZ}^*	-	20	-	25	-	30	ns
Output Hold from Address Change	t_{OH}	10	-	10	-	10	-	ns
$\overline{LB}$, $\overline{UB}$ Access Time	t_{BA}	-	55	-	70	-	100	ns
$\overline{LB}$, $\overline{UB}$ to High-Z Output	t_{BHZ}	-	25	-	30	-	40	ns
$\overline{LB}$, $\overline{UB}$ to Low-Z Output	t_{BLZ}	10	-	10	-	10	-	ns

(2) WRITE CYCLE

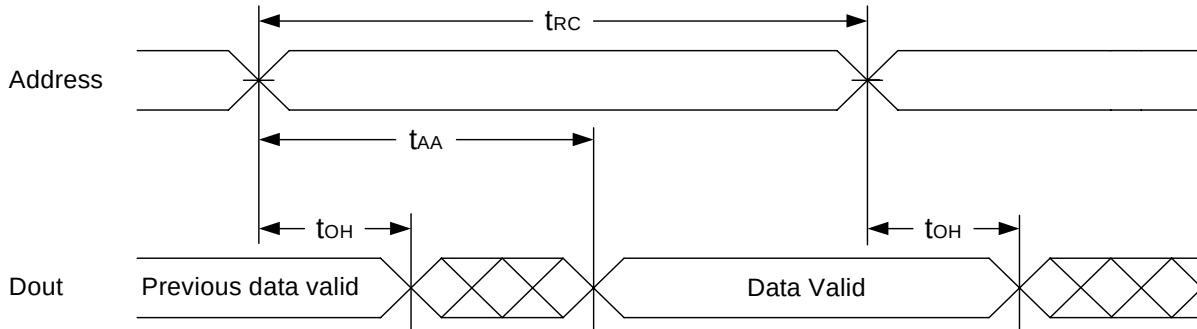
PARAMETER	SYMBOL	UT62L12816(I)-55 $V_{CC} = 2.7\text{V} \sim 3.6\text{V}$		UT62L12816(I)-70 $V_{CC} = 2.5\text{V} \sim 3.6\text{V}$		UT62L12816(I)-100 $V_{CC} = 2.5\text{V} \sim 3.6\text{V}$		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Write Cycle Time	t_{WC}	55	-	70	-	100	-	ns
Address Valid to End of Write	t_{AW}	50	-	60	-	80	-	ns
Chip Enable to End of Write	t_{CW}	50	-	60	-	80	-	ns
Address Set-up Time	t_{AS}	0	-	0	-	0	-	ns
Write Pulse Width	t_{WP}	45	-	55	-	70	-	ns
Write Recovery Time	t_{WR}	0	-	0	-	0	-	ns
Data to Write Time Overlap	t_{DW}	25	-	30	-	40	-	ns
Data Hold from End of Write Time	t_{DH}	0	-	0	-	0	-	ns
Output Active from End of Write	t_{OW}^*	5	-	5	-	5	-	ns
Write to Output in High Z	t_{WHZ}^*	-	30	-	30	-	40	ns
$\overline{LB}$, $\overline{UB}$ Valid to End of Write	t_{BW}	45	-	60	-	80	-	ns

* These parameters are guaranteed by device characterization, but not production tested.

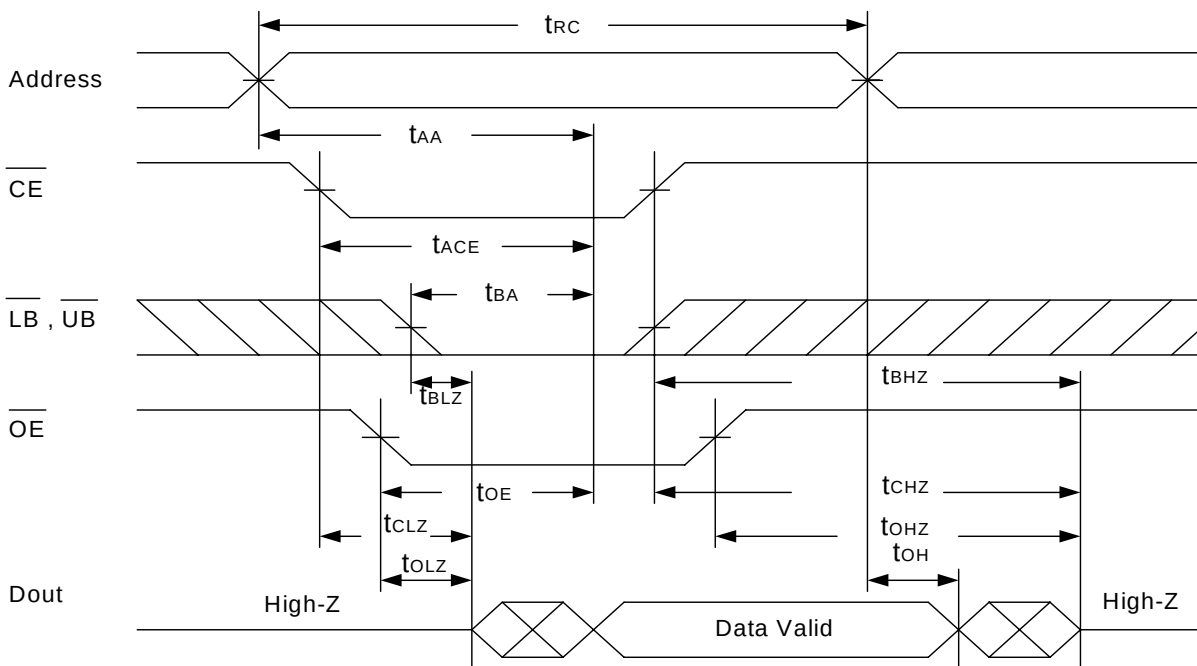


TIMING WAVEFORMS

READ CYCLE 1 (Address Controlled) (1,2)



READ CYCLE 2 ($\overline{CE}$ and $\overline{OE}$ Controlled) (1,3,4,5)



Notes :

1. $\overline{WE}$ is high for read cycle.
2. Device is continuously selected $\overline{OE}$ = low, $\overline{CE}$ = low, $\overline{LB}$ or $\overline{UB}$ = low.
3. Address must be valid prior to or coincident with $\overline{CE}$ = low, $\overline{LB}$ or $\overline{UB}$ = low transition; otherwise t_{AA} is the limiting parameter.
4. t_{CLZ} , t_{BLZ} , t_{OLZ} , t_{CHZ} , t_{BHZ} and t_{OHZ} are specified with C_L = 5pF. Transition is measured ± 500 mV from steady state.
5. At any given temperature and voltage condition, t_{CHZ} is less than t_{CLZ} , t_{BHZ} is less than t_{BLZ} , t_{OHZ} is less than t_{OLZ} .

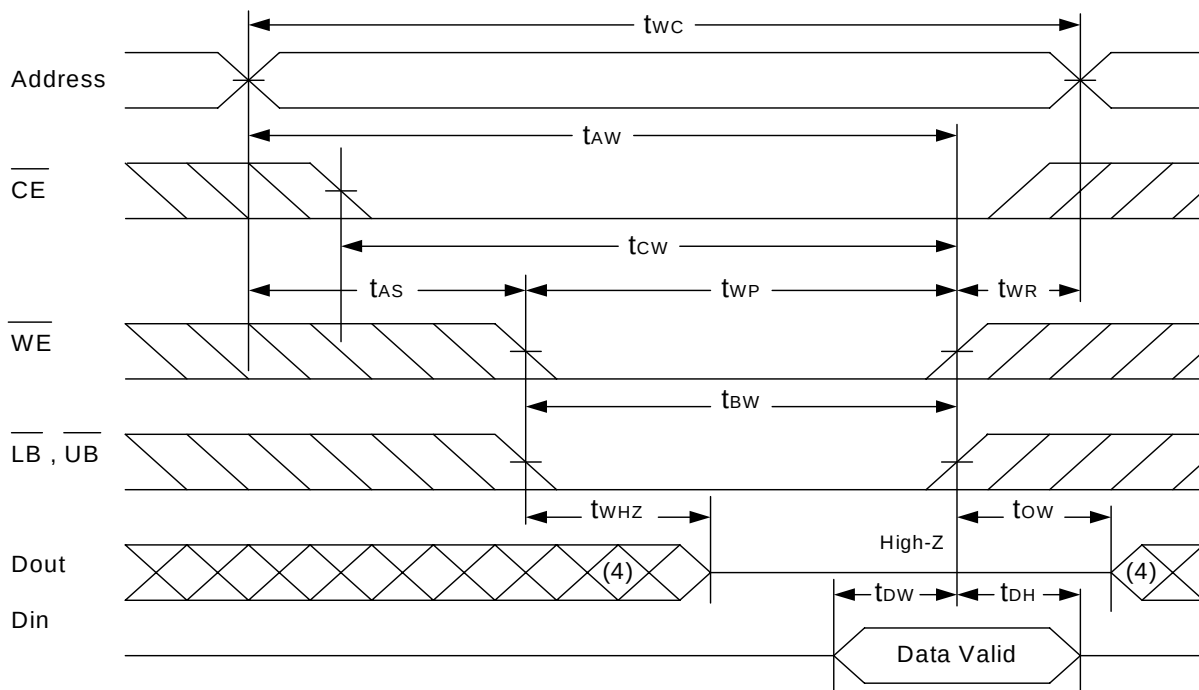


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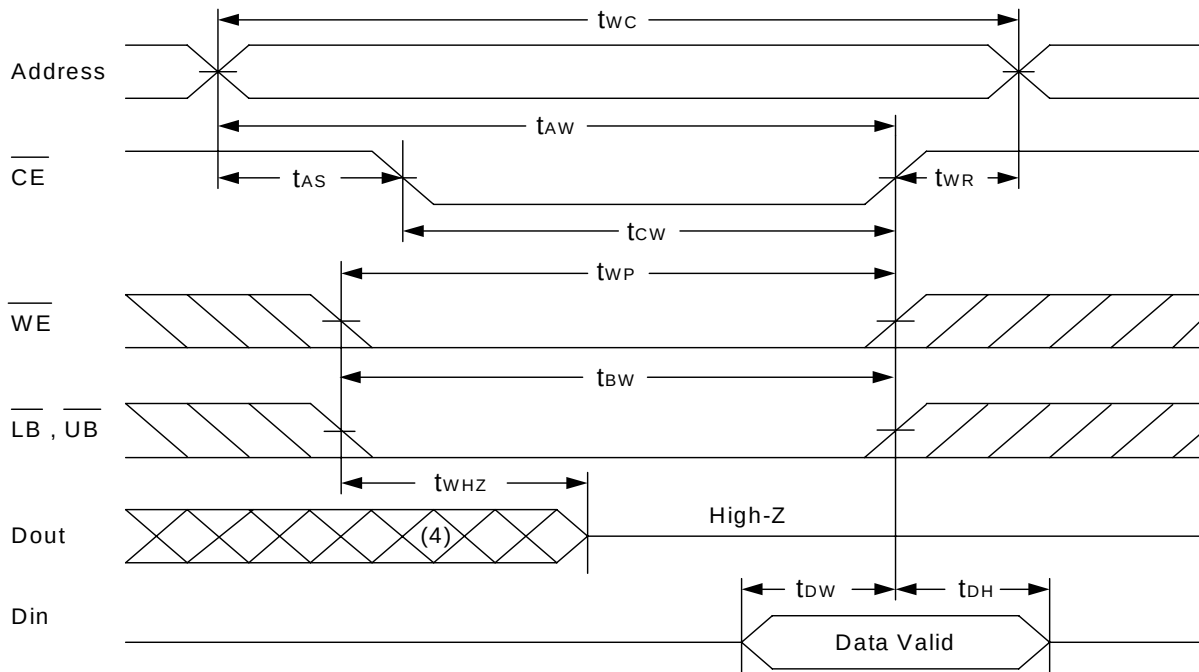
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WRITE CYCLE 1 ($\overline{WE}$ Controlled) (1,2,3,5,6)

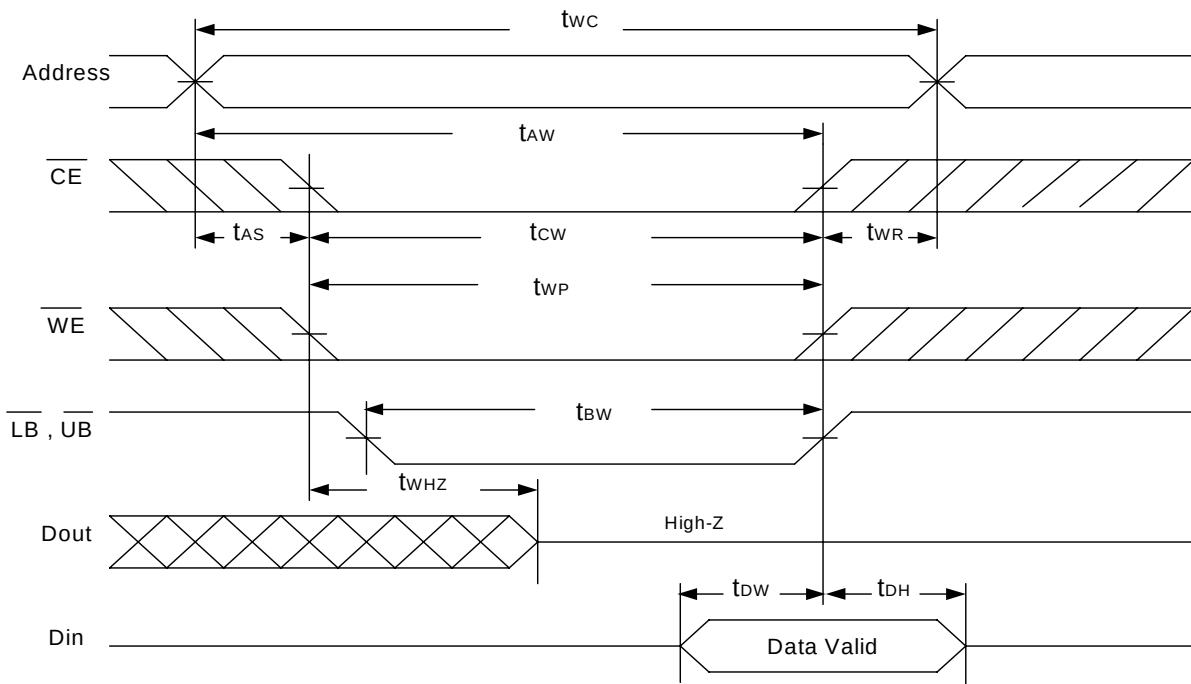


WRITE CYCLE 2 ($\overline{CE}$ Controlled) (1,2,5,6)





WRITE CYCLE 3 ($\overline{LB}$, $\overline{UB}$ Controlled) (1,2,5,6)

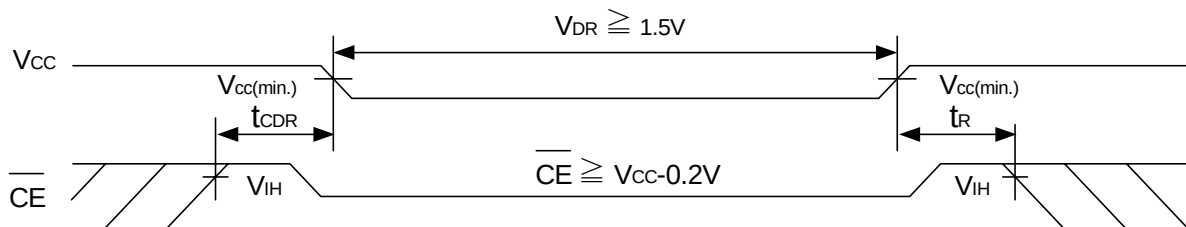
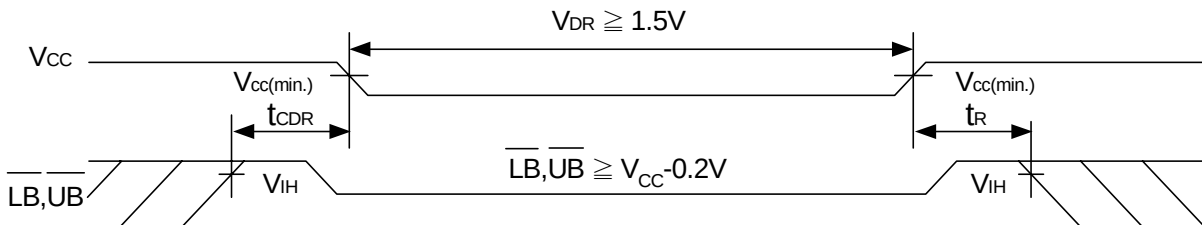


Notes :

1. $\overline{WE}$, $\overline{CE}$, $\overline{LB}$, $\overline{UB}$ must be high during all address transitions.
2. A write occurs during the overlap of a low $\overline{CE}$, low $\overline{WE}$, $\overline{LB}$ or $\overline{UB}$ = low.
3. During a $\overline{WE}$ controlled write cycle with $\overline{OE}$ low, t_{WP} must be greater than $t_{WHZ} + t_{BW}$ to allow the drivers to turn off and data to be placed on the bus.
4. During this period, I/O pins are in the output state, and input signals must not be applied.
5. If the $\overline{CE}$, $\overline{LB}$, $\overline{UB}$ low transition occurs simultaneously with or after $\overline{WE}$ low transition, the outputs remain in a high impedance state.
6. t_{OW} and t_{WHZ} are specified with $C_L = 5pF$. Transition is measured $\pm 500mV$ from steady state.

**DATA RETENTION CHARACTERISTICS** ($T_A = -40^{\circ}\text{C}$ to 85°C)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
V _{CC} for Data Retention	V _{DR}	$\overline{\text{CE}} \geq V_{\text{CC}} - 0.2\text{V}$	1.5	-	3.6	V
Data Retention Current	I _{DR}	V _{CC} =1.5V	- L	-	50	μA
		$\overline{\text{CE}} \geq V_{\text{CC}} - 0.2\text{V}$	- LL	-	5	μA
Chip Disable to Data Retention Time	t _{CDR}	See Data Retention Waveforms (below)	0	-	-	ms
Recovery Time	t _R		5	-	-	ms

DATA RETENTION WAVEFORM**Low V_{CC} Data Retention Waveform (1)** ($\overline{\text{CE}}$ controlled)**Low V_{CC} Data Retention Waveform (2)** ($\overline{\text{LB}}, \overline{\text{UB}}$ controlled)



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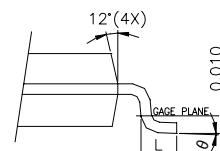
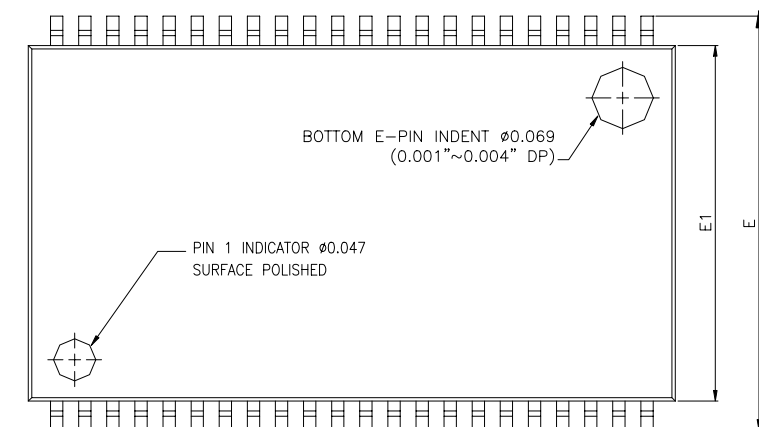
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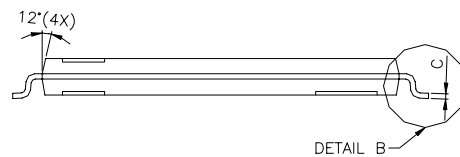
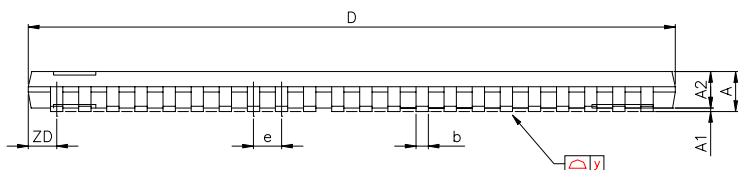
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PACKAGE OUTLINE DIMENSION

44-pin 400mil TSOP-II Package Outline Dimension

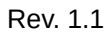


DETAIL B



DETAIL B

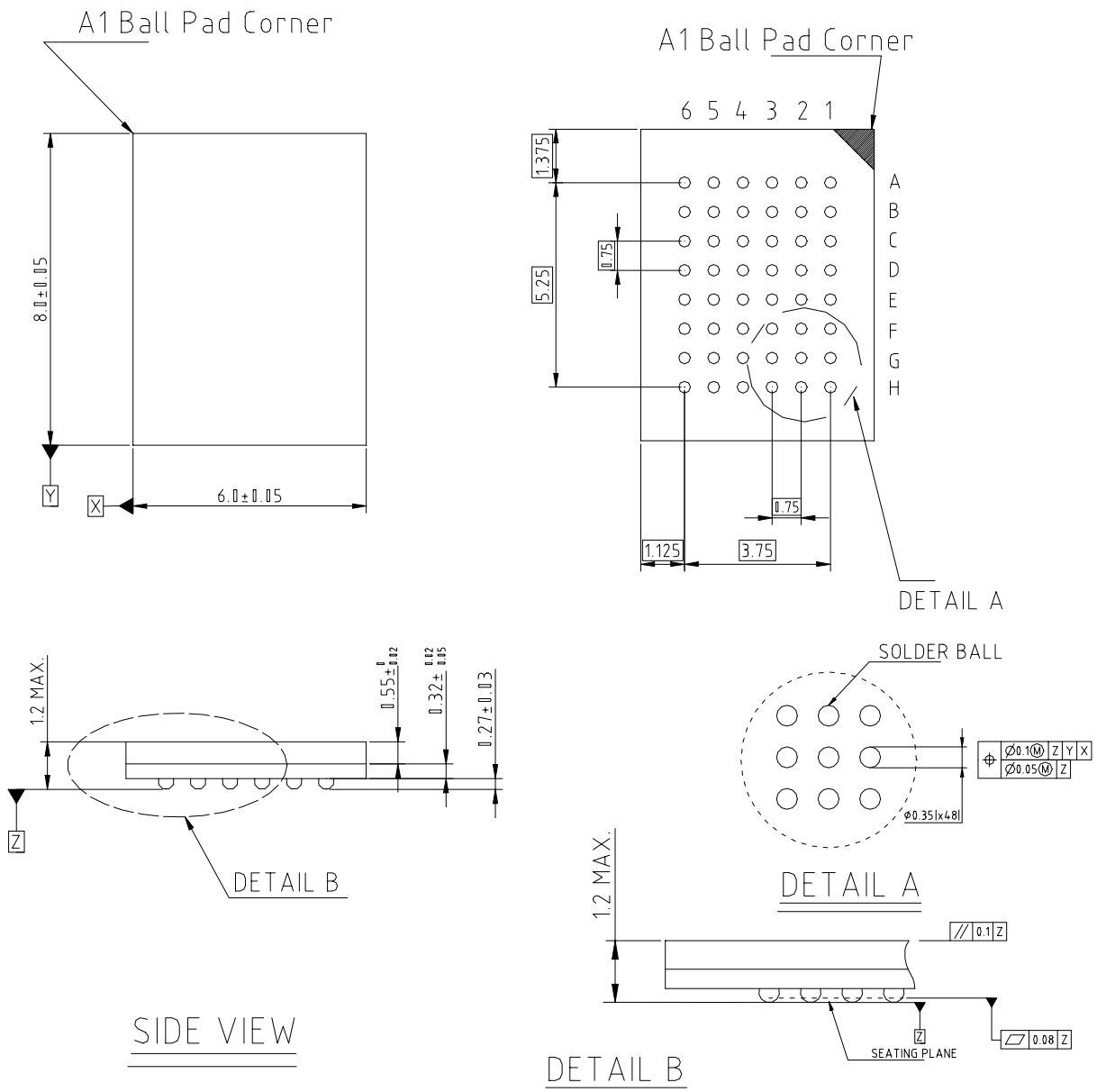
SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHS		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.00	-	1.20	0.039	-	0.047
A1	0.05	-	0.15	0.002	-	0.006
A2	0.95	1.00	1.05	0.037	0.039	0.041
b	0.30	0.35	0.45	0.012	0.014	0.018
c	0.12	-	0.21	0.0047	-	0.083
D	18.313	18.415	18.517	0.721	0.725	0.728
E	11.854	11.836	11.838	0.460	0.466	0.470
E1	10.058	10.180	10.282	0.398	0.400	0.404
e	-	0.800	-	-	0.0315	-
L	0.40	0.50	0.60	0.0157	0.020	0.0236
2D	-	0.805	-	-	0.0317	-
y	0.00	-	0.076	0.000	-	0.003
Θ	0°	-	5°	0°	-	5°



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48-pin 6mm × 8mm TFBGA Package Outline Dimension





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ORDERING INFORMATION**INDUSTRIAL TEMPERATURE**

PART NO.	ACCESS TIME (ns)	STANDBY CURRENT (μ A) max. $T_A = 0^{\circ}\text{C}$ to 50°C	PACKAGE
UT62L12816MC-55LI	55	20	44 PIN TSOP- II
UT62L12816MC-55LLI	55	3	44 PIN TSOP- II
UT62L12816MC-70LI	70	20	44 PIN TSOP- II
UT62L12816MC-70LLI	70	3	44 PIN TSOP- II
UT62L12816MC-100LI	100	20	44 PIN TSOP- II
UT62L12816MC-100LLI	100	3	44 PIN TSOP- II
UT62L12816BS-55LI	55	20	48 PIN TFBGA
UT62L12816BS-55LLI	55	3	48 PIN TFBGA
UT62L12816BS-70LI	70	20	48 PIN TFBGA
UT62L12816BS-70LLI	70	3	48 PIN TFBGA
UT62L12816BS-100LI	100	20	48 PIN TFBGA
UT62L12816BS-100LLI	100	3	48 PIN TFBGA

ORDERING INFORMATION (for lead free product)**INDUSTRIAL TEMPERATURE**

PART NO.	ACCESS TIME (ns)	STANDBY CURRENT (μ A) max. $T_A = 0^{\circ}\text{C}$ to 50°C	PACKAGE
UT62L12816MCL-55LI	55	20	44 PIN TSOP- II
UT62L12816MCL-55LLI	55	3	44 PIN TSOP- II
UT62L12816MCL-70LI	70	20	44 PIN TSOP- II
UT62L12816MCL-70LLI	70	3	44 PIN TSOP- II
UT62L12816MCL-100LI	100	20	44 PIN TSOP- II
UT62L12816MCL-100LLI	100	3	44 PIN TSOP- II
UT62L12816BSL-55LI	55	20	48 PIN TFBGA
UT62L12816BSL-55LLI	55	3	48 PIN TFBGA
UT62L12816BSL-70LI	70	20	48 PIN TFBGA
UT62L12816BSL-70LLI	70	3	48 PIN TFBGA
UT62L12816BSL-100LI	100	20	48 PIN TFBGA
UT62L12816BSL-100LLI	100	3	48 PIN TFBGA



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